

**Notice of References Cited**

Application/Control No.

10/762,181

Applicant(s)/Patent Under  
Reexamination  
MOKHLESI ET AL.

Examiner

Huan Hoang

Art Unit

2827

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,784,484	08-2004	Blomme et al.	257/321
*	B	US-6,790,782	09-2004	Yang et al.	438/706
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	"An Empeirical Model for Charge Leakage Through Oxide-Nitride-Oxide Interpoly Dielectric In Stacked-Gate Flash Memory Devices", Jang Han Kim, Jung Bum Choi, Bong Jo Shin and Kuen Hyung Park, Semiconductor Science and Technology 18 (2003) pp. 258-162.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.